

Plastic-Encapsulate Transistors

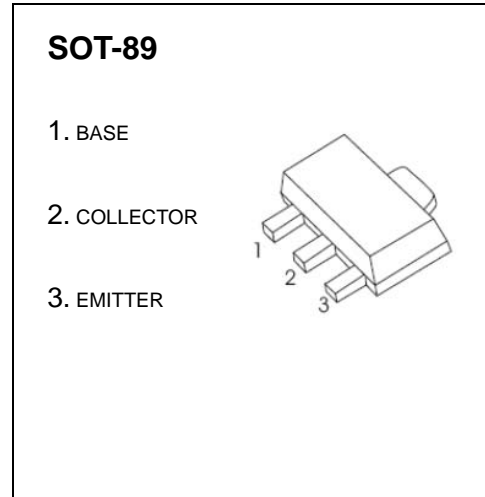
TRANSISTOR(PNP)

FEATURES

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Continuous Collector Current	-2	A
I _{CM}	Peak Pluse Current	-3	A
P _C	Collector Power dissipation	500	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-500mA	82		270	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-50mA			-0.35	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A, f=100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		36		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	82-180	120-270
Marking	AGP	AGQ

Typical Characteristics

